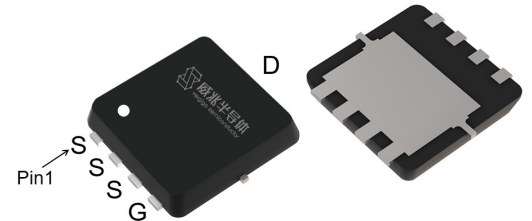


Features

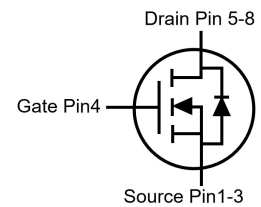
- Enhancement mode
- Very low on-resistance
- VitoMOS® II Technology
- Fast Switching and High efficiency
- 100% Avalanche Tested

V_{DS}	30	V
$R_{DS(on),TYP@ V_{GS}=10V}$	3.6	mΩ
$R_{DS(on),TYP@ V_{GS}=4.5V}$	5.6	mΩ
$I_D(\text{Silicon Limited})$	67	A
$I_D(\text{Package Limited})$	40	A

PDFN3333



Part ID	Package Type	Marking	Packing
VS3615GE	PDFN3333	3615GE	5000PCS/Reel



Maximum ratings, at $T_A = 25^\circ\text{C}$, unless otherwise specified

Symbol	Parameter		Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage		30	V
V_{GS}	Gate-Source voltage		± 20	V
I_S	Diode continuous forward current	$T_C = 25^\circ\text{C}$	67	A
I_D	Continuous drain current @ $V_{GS}=10V$ (Silicon limited)	$T_C = 25^\circ\text{C}$	67	A
I_D	Continuous drain current @ $V_{GS}=10V$ (Silicon limited)	$T_C = 100^\circ\text{C}$	42	A
I_D	Continuous drain current @ $V_{GS}=10V$ (Package limited)	$T_C = 25^\circ\text{C}$	40	A
I_{DM}	Pulse drain current tested ①	$T_C = 25^\circ\text{C}$	170	A
I_{DSM}	Continuous drain current @ $V_{GS}=10V$	$T_A = 25^\circ\text{C}$	23	A
		$T_A = 70^\circ\text{C}$	18	A
E_{AS}	Avalanche energy, single pulsed ②		25	mJ
P_D	Maximum power dissipation	$T_C = 25^\circ\text{C}$	31	W
		$T_C = 100^\circ\text{C}$	13	W
P_{DSM}	Maximum power dissipation ③	$T_A = 25^\circ\text{C}$	3.6	W
		$T_A = 70^\circ\text{C}$	2.3	W
$T_{STG,TJ}$	Storage and Junction Temperature Range		-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typical	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	4	4.8	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	35	42	$^\circ\text{C/W}$

Electrical Characteristics

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ T _j =25°C (unless otherwise stated)						
V(BR)DSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current(T _j =25°C)	V _{DS} =30V,V _{GS} =0V	--	--	1	μA
	Zero Gate Voltage Drain Current(T _j =125°C)	V _{DS} =30V,V _{GS} =0V	--	--	100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V,V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ,I _D =250μA	1.0	1.6	2.1	V
R _{DS(on)}	Drain-Source On-State Resistance ④	V _{GS} =10V, I _D =20A	--	3.6	4.7	mΩ
		(T _j =100°C)	--	4.2	--	mΩ
R _{DS(on)}	Drain-Source On-State Resistance ④	V _{GS} =4.5V, I _D =10A	--	5.6	7.3	mΩ
Dynamic Electrical Characteristics @ T _j = 25°C (unless otherwise stated)						
C _{iss}	Input Capacitance	V _{DS} =15V,V _{GS} =0V, f=1MHz	550	1095	1915	pF
C _{oss}	Output Capacitance		295	590	1035	pF
C _{rss}	Reverse Transfer Capacitance		30	70	115	pF
R _g	Gate Resistance	f=1MHz	0.2	1.3	5	Ω
Q _g (10V)	Total Gate Charge	V _{DS} =15V,I _D =20A, V _{GS} =10V	--	21	37	nC
Q _g (4.5V)	Total Gate Charge		--	11	19	nC
Q _{gs}	Gate-Source Charge		--	3.5	6.1	nC
Q _{gd}	Gate-Drain Charge		--	4.6	8.1	nC
Switching Characteristics						
T _d (on)	Turn-on Delay Time	V _{DD} =15V, I _D =20A, R _G =3Ω, V _{GS} =10V	--	6.6	--	ns
T _r	Turn-on Rise Time		--	58	--	ns
T _d (off)	Turn-Off Delay Time		--	19	--	ns
T _f	Turn-Off Fall Time		--	9.4	--	ns
Source- Drain Diode Characteristics@ T _j = 25°C (unless otherwise stated)						
V _{SD}	Forward on voltage	I _{SD} =20A,V _{GS} =0V	--	0.8	1.2	V
T _{rr}	Reverse Recovery Time	I _{sd} =20A, V _{GS} =0V	--	18	36	ns
Q _{rr}	Reverse Recovery Charge	di/dt=100A/μs	--	4.3	8.6	nC

NOTE: ① Single pulse; pulse width $\leq 100\mu s$.

② Limited by T_{Jmax} , starting $T_J = 25^{\circ}\text{C}$, $L = 0.5\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 10A$, $V_{GS} = 10V$. Part not recommended for use above this value

③ The power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C .

④ Pulse width $\leq 380\mu s$; duty cycles $\leq 2\%$.

Typical Characteristics

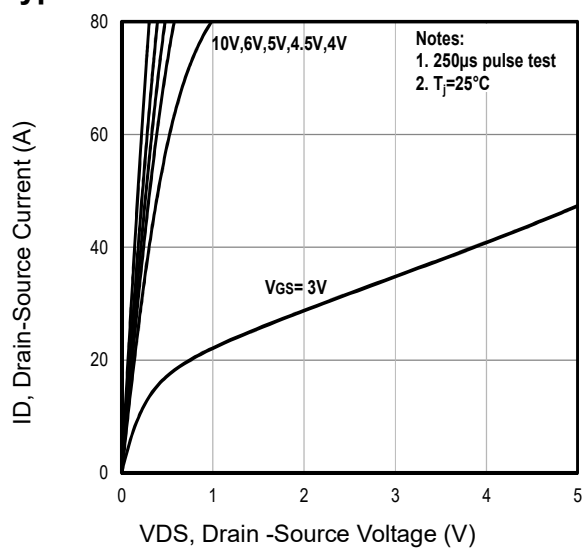


Fig1. Typical Output Characteristics

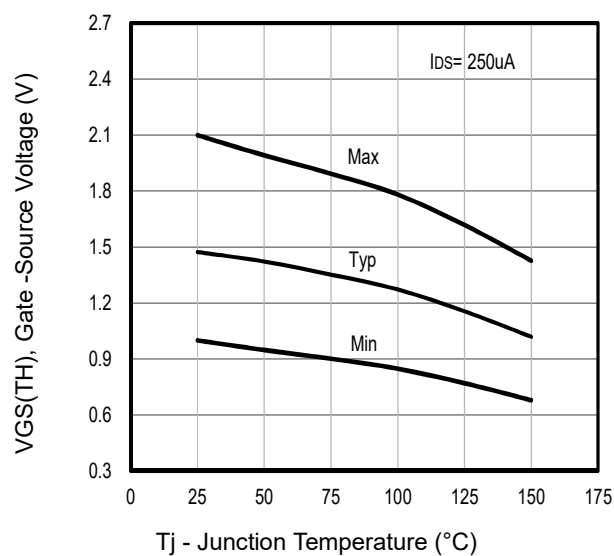


Fig2. $V_{GS(TH)}$ Gate-Source Voltage Vs. T_j

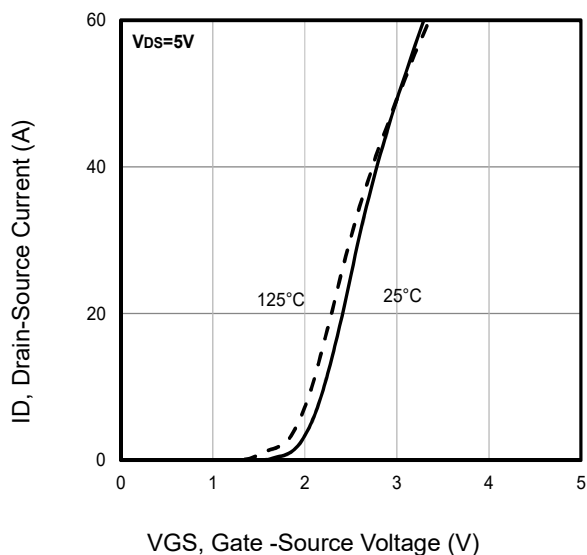


Fig3. Typical Transfer Characteristics

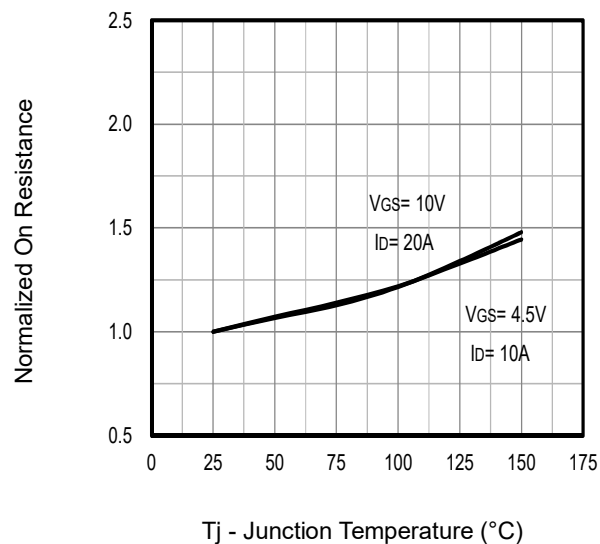


Fig4. Typical Normalized On-Resistance Vs. T_j

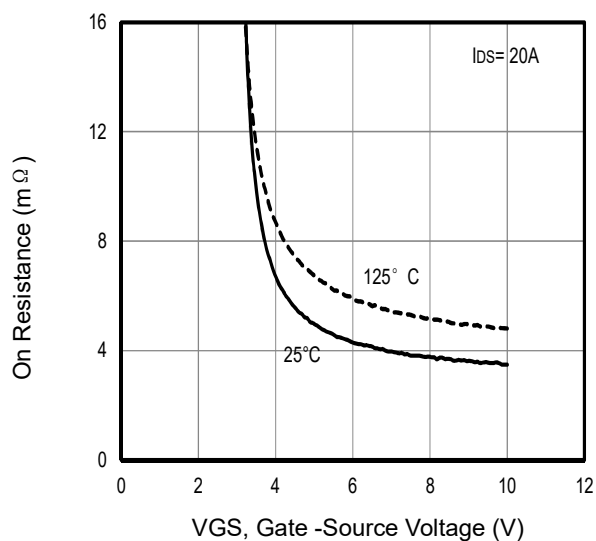


Fig5. Typical On Resistance Vs Gate-Source Voltage

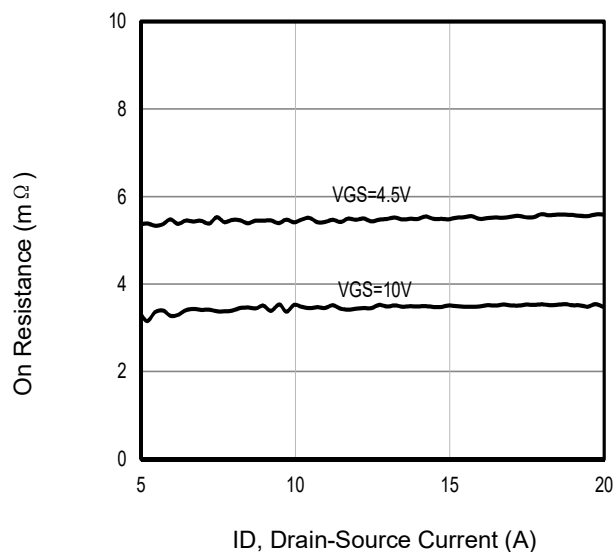


Fig6. Typical On Resistance Vs Drain Current and Gate

Typical Characteristics

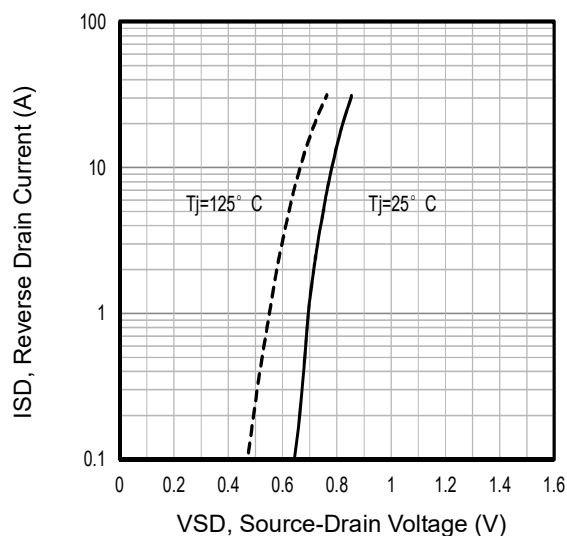


Fig7. Typical Source-Drain Diode Forward Voltage

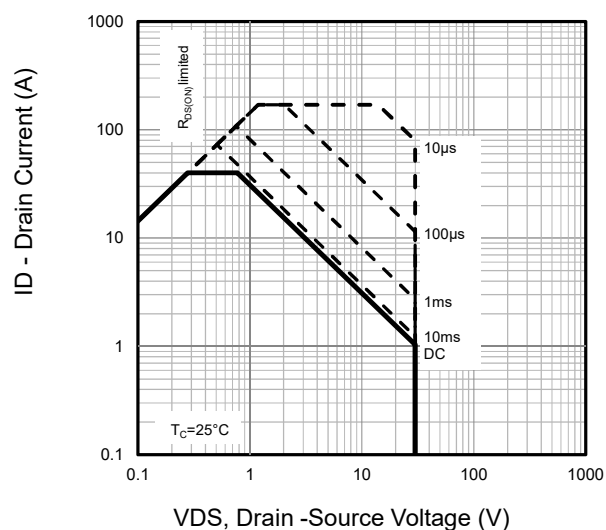


Fig8. Maximum Safe Operating Area

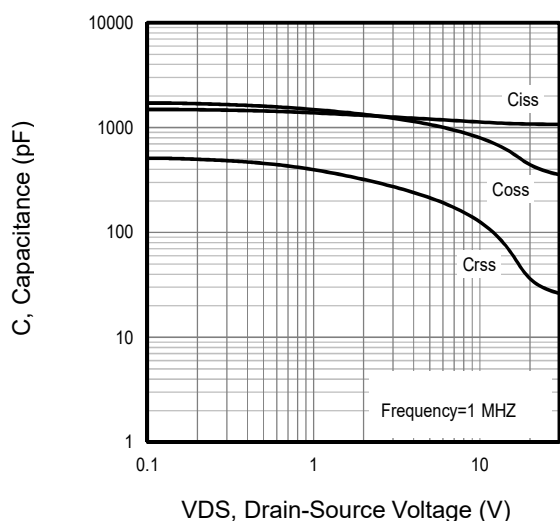


Fig9. Typical Capacitance Vs. Drain-Source Voltage

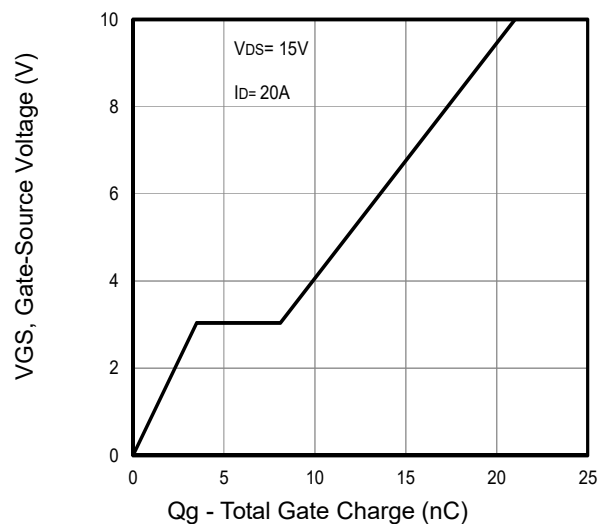


Fig10. Typical Gate Charge Vs. Gate-Source Voltage

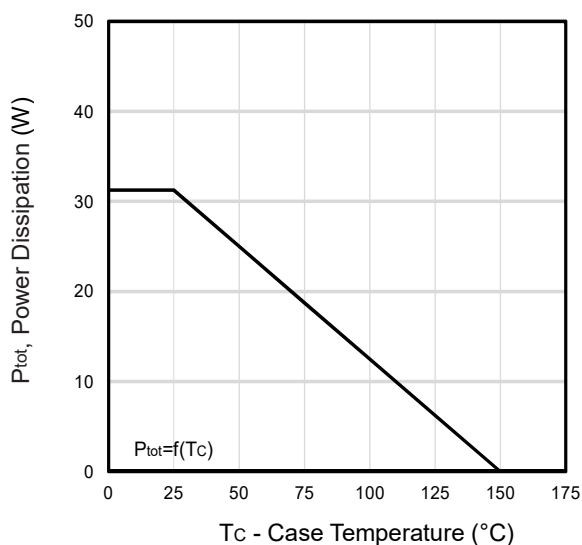


Fig11. Power Dissipation Vs. Case Temperature

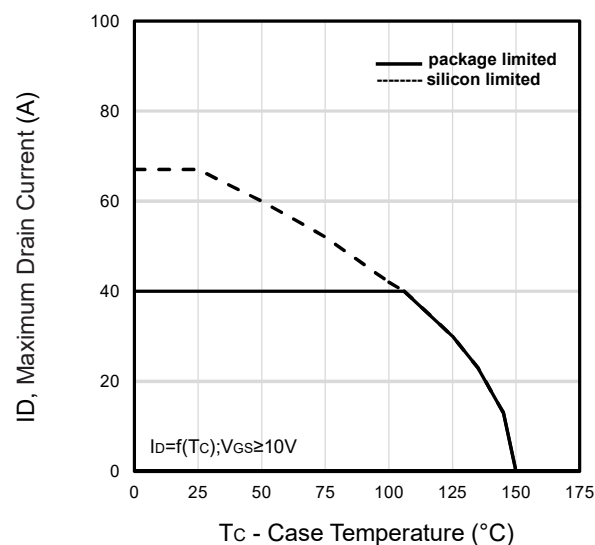


Fig12. Maximum Drain Current Vs. Case Temperature

Typical Characteristics

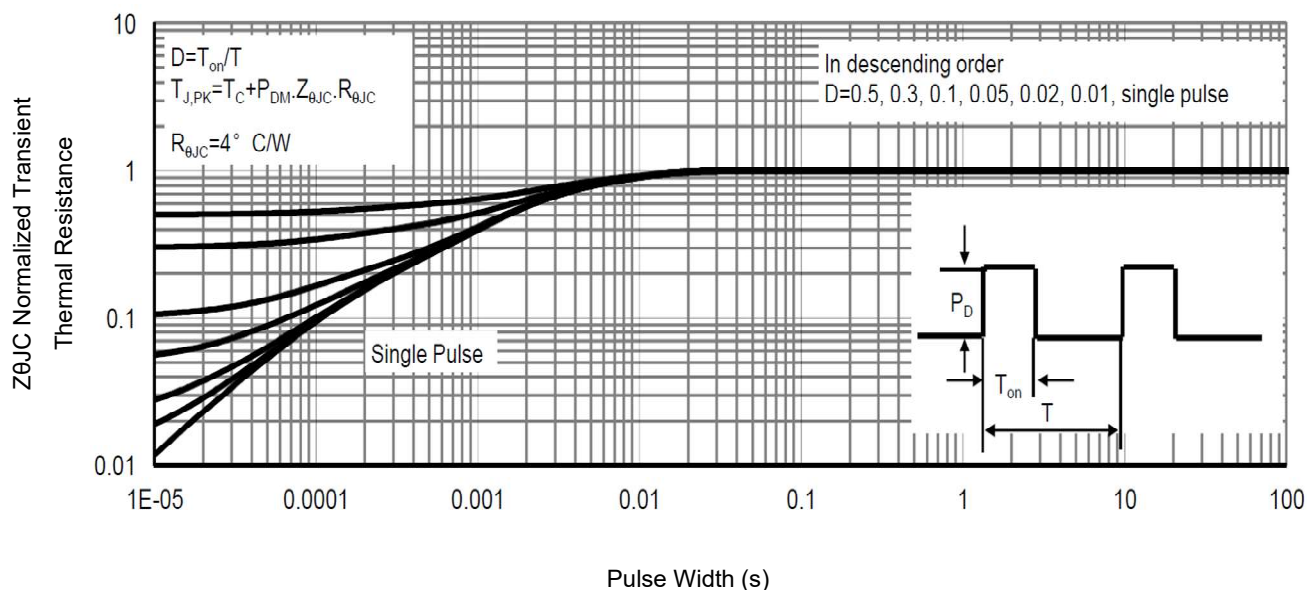


Fig13 . Normalized Maximum Transient Thermal Impedance

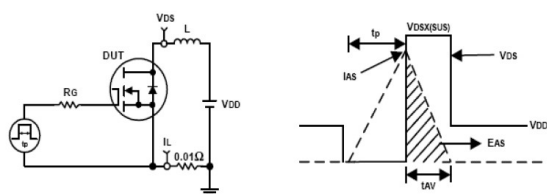


Fig14. Unclamped Inductive Test Circuit and waveforms

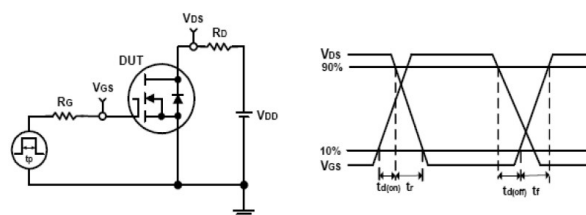
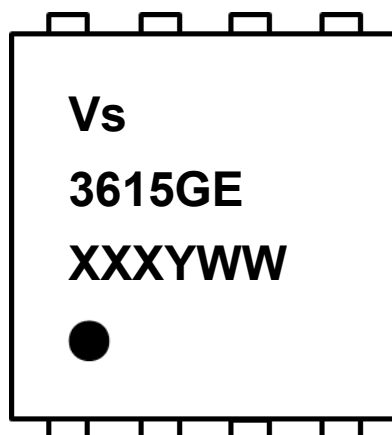


Fig15. Switching Time Test Circuit and waveforms

Marking Information

1st line: Vergiga Code (Vs)

2nd line: Part Number (3615GE)

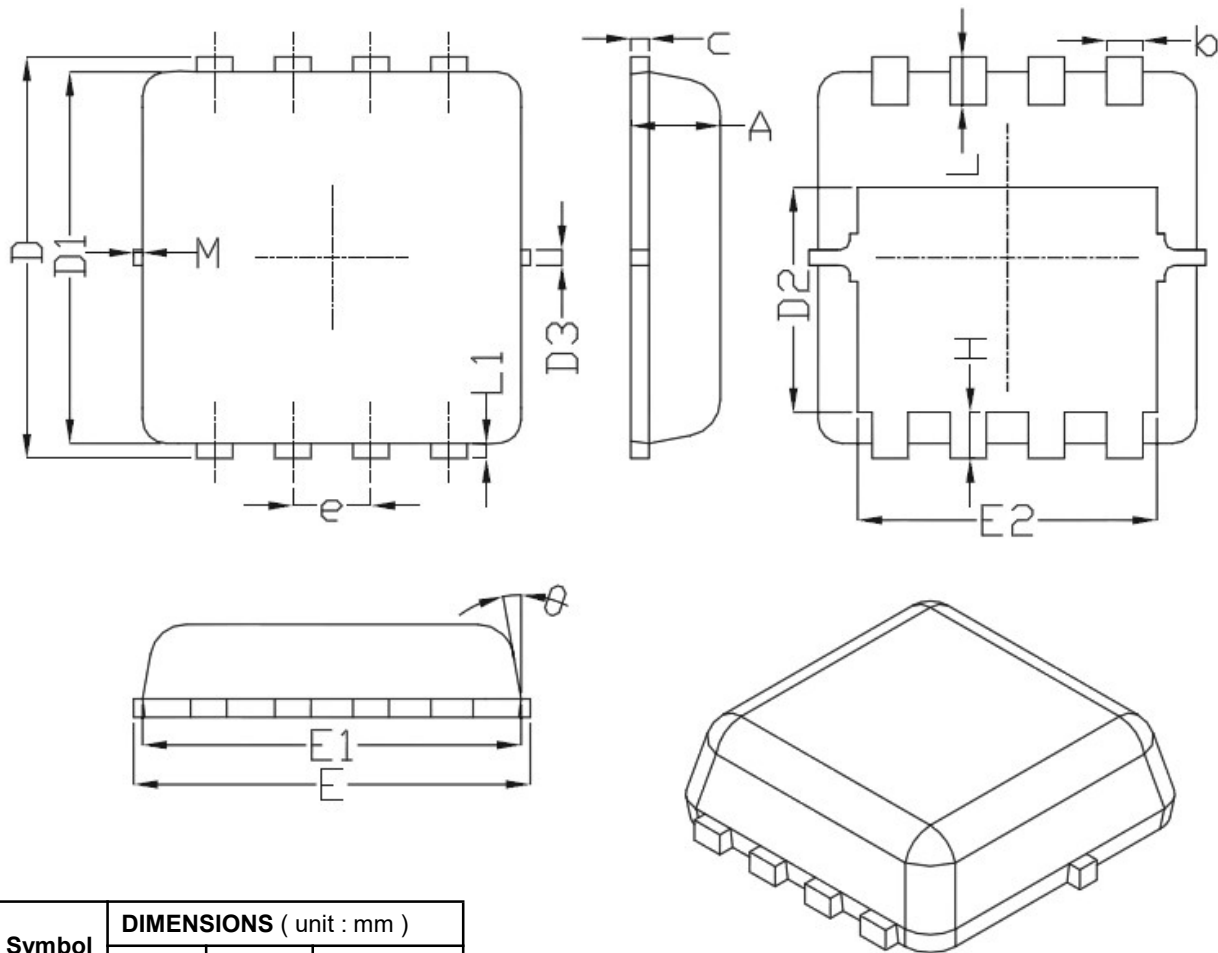
3rd line: Date code (XXXYWW)

XXX: Wafer Lot Number Code , code changed with Lot Number

Y: Year Code , refer to table below

WW: Week Code (01 to 53)

Code	C	D	E	F	G	H	J	K	L	M	N	P	Q	R	S	T
Year	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030

PDFN3333 Package Outline Data


Symbol	DIMENSIONS (unit : mm)		
	Min	Typ	Max
A	0.70	0.75	0.80
b	0.25	0.30	0.35
C	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.78	1.88	1.98
D3	--	0.13	--
E	3.00	3.20	3.40
E1	3.00	3.10	3.20
E2	2.39	2.49	2.59
e	0.65 BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	--	0.13	--
θ	--	10°	12°
M	*	*	0.15
* Not specified			

Notes:

1. Follow JEDEC MO-240 variation CA.
2. Dimensions "D1" and "E1" do NOT include mold flash protrusions or gate burrs.
3. Dimensions "D1" and "E1" include interterminal flash or protrusion. Interterminal flash or protrusion shall not exceed 0.25mm per side.

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